

High Voltage IGBT Low $V_{CE(sat)}$

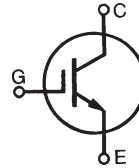
IXGH 40N120A2 IXGT 40N120A2

$$V_{CES} = 1200 \text{ V}$$

$$I_{C25} = 75 \text{ A}$$

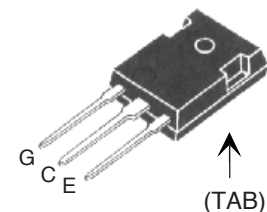
$$V_{CE(sat)} \leq 2.0 \text{ V}$$

Preliminary Data Sheet

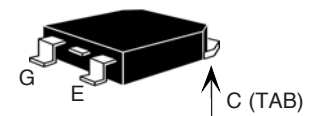


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$, IGBT chip capability	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	40	A
I_{CM}	$T_J \leq 150^\circ\text{C}$, $t_p < 300 \mu\text{s}$	160	A
SSOA	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 5 \Omega$	$I_{CM} = 80$	A
(RBSOA)	Clamped inductive load, $V_{CE} < 960 \text{ V}$		
P_C	$T_C = 25^\circ\text{C}$	360	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 seconds	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting torque (ixgh)	1.3/10	Nm/lb.in.
Weight	(IXGH)	6.0	g
	(IXGT)	4.0	g

TO-247 (IXFH)



TO-268 (IXGT)



G = Gate
E = Emitter
C = Collector
TAB = Collector

Features

- International standard packages
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity

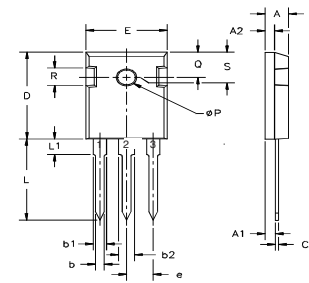
Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Capacitor discharge

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 1 \text{ mA}$, $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$			50 μA 1 mA $T_J = 125^\circ\text{C}$
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C110}$, $V_{GE} = 15 \text{ V}$			2.0 V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = I_{C110}, V_{CE} = 10\text{ V}$	28	40	S
$I_{C(ON)}$	$V_{GE} = 10\text{ V}, V_{CE} = 10\text{ V}$		195	A
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		3150	pF
C_{oes}			165	pF
C_{res}			70	pF
Q_g	$I_C = I_{C110}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		136	nC
Q_{ge}			19	nC
Q_{gc}			54	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$		22	ns
t_{ri}	$I_C = I_{C110}, V_{GE} = 15\text{ V}$		41	ns
$t_{d(off)}$	$V_{CE} = 0.8 V_{CES}, R_G = 2\ \Omega$	420	800	ns
t_{fi}		800	1200	ns
E_{off}		15	25	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$		19	ns
t_{ri}	$I_C = I_{C110}, V_{GE} = 15\text{ V}$		36	ns
E_{on}	$V_{CE} = 0.8 V_{CES}, R_G = 2\ \Omega$		3.5	mJ
$t_{d(off)}$		730		ns
t_{fi}		1570		ns
E_{off}		35		mJ
R_{thJC}			0.35	K/W
R_{thCS}	(TO-247)		0.25	K/W

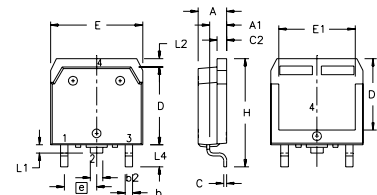
TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S			242 BSC	

TO-268 Outline (IXGT)



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

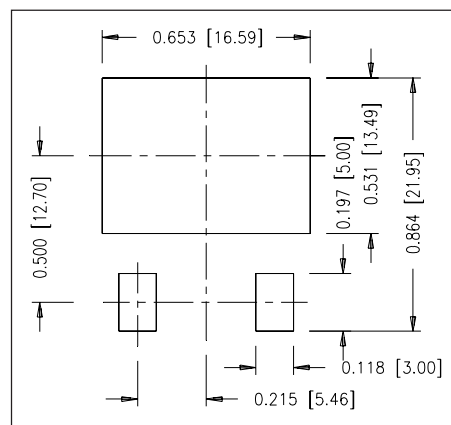
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e		.215 BSC		5.45 BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃		.010 BSC		0.25 BSC
L ₄	.150	.161	3.80	4.10

Note 1: Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a subjective pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

TO-268: Min. Recommended Footprint



IXYS reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585
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4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463

Fig. 1. Output Characteristics
@ 25°C

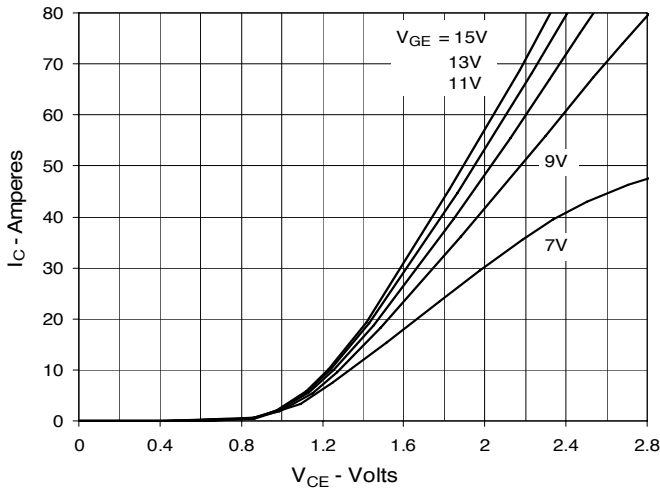


Fig. 2. Extended Output Characteristics
@ 25°C

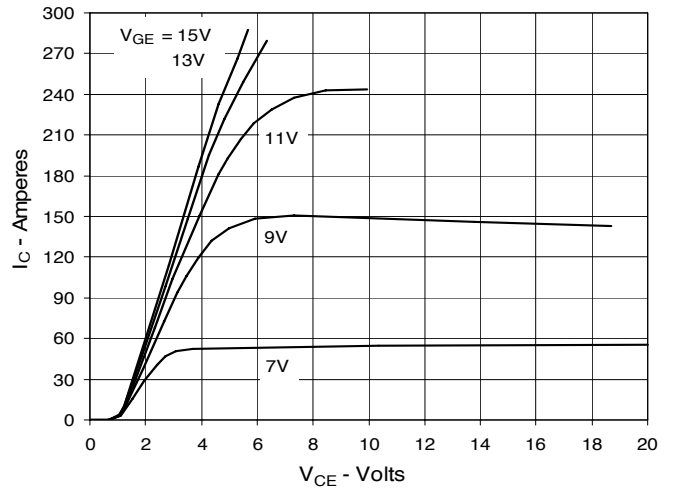


Fig. 3. Output Characteristics
@ 125°C

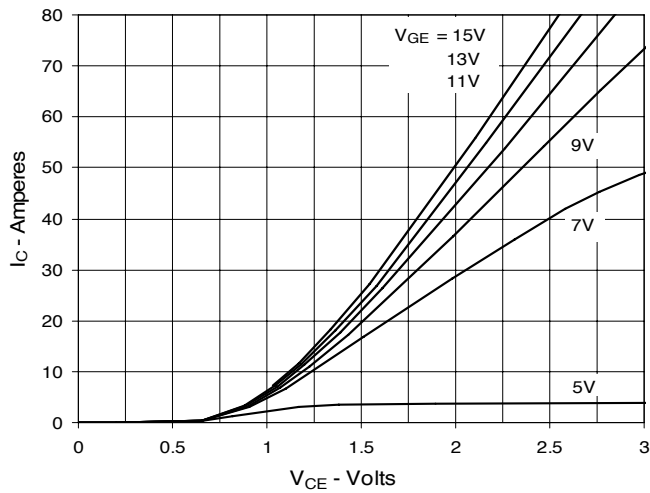


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

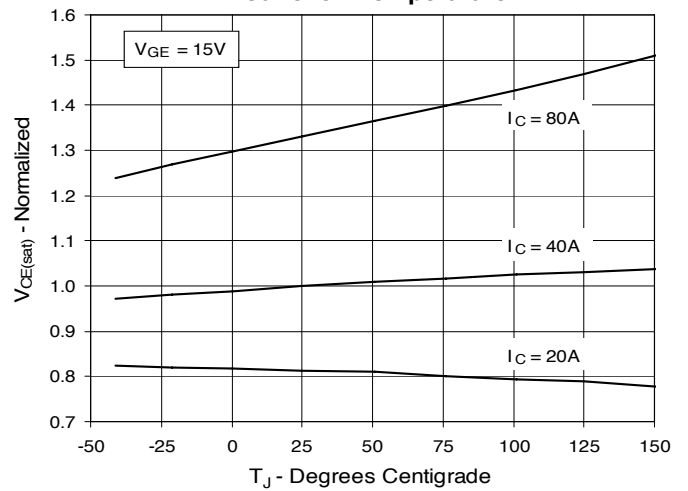


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

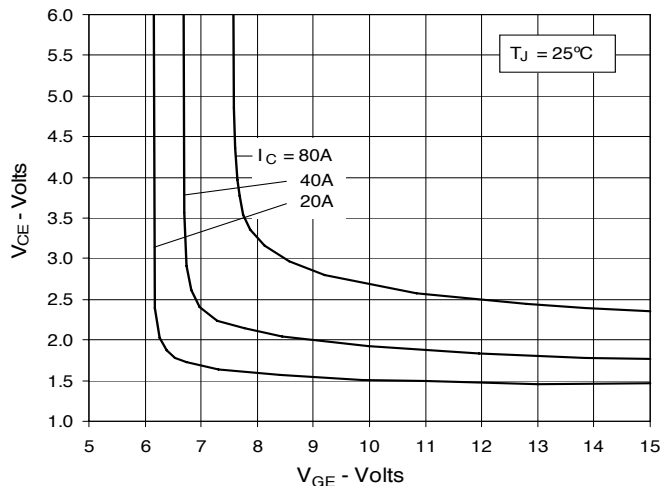


Fig. 6. Input Admittance

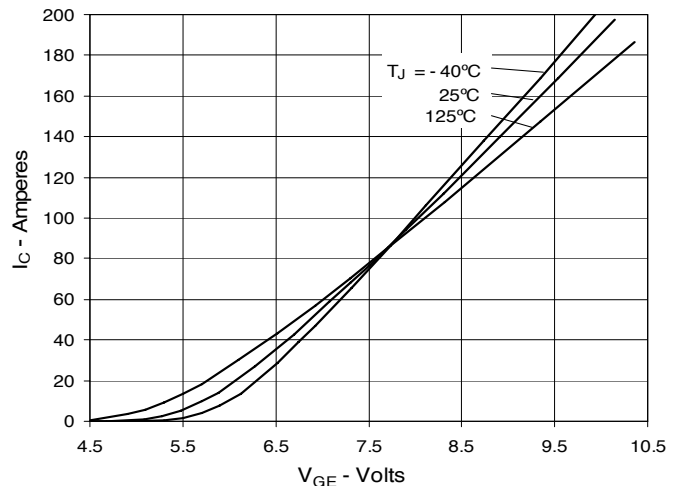


Fig. 7. Transconductance

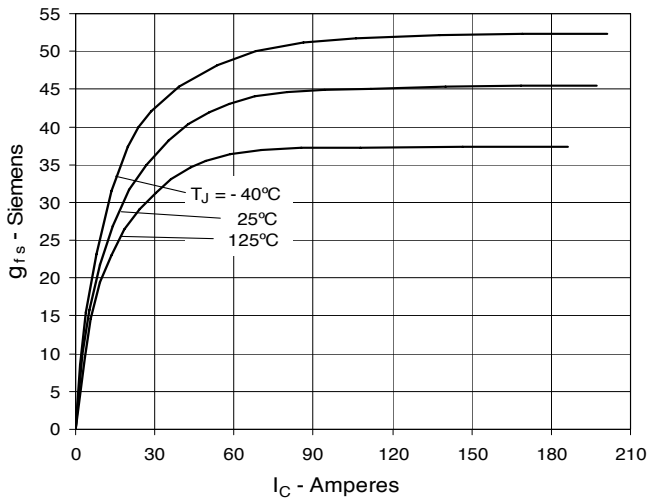


Fig. 8. Inductive Turn-off Switching Times vs. Gate Resistance

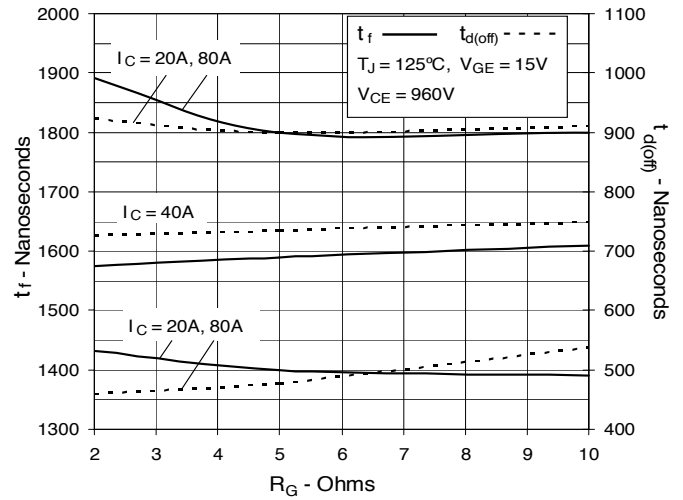


Fig. 9. Inductive Turn-off Switching Times vs. Collector Current

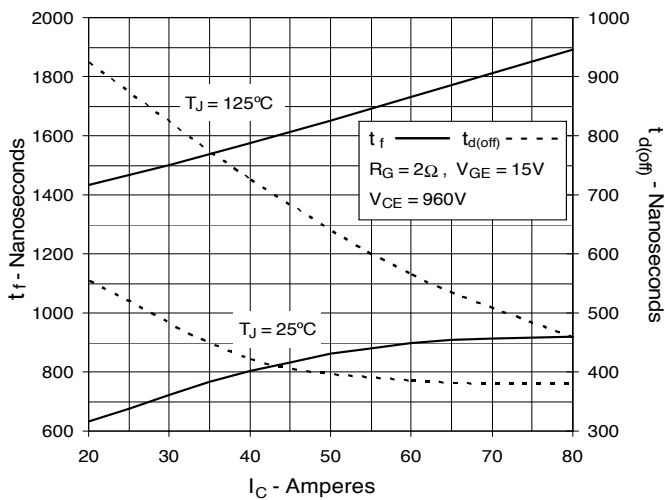


Fig. 10. Inductive Turn-off Switching Times vs. Junction Temperature

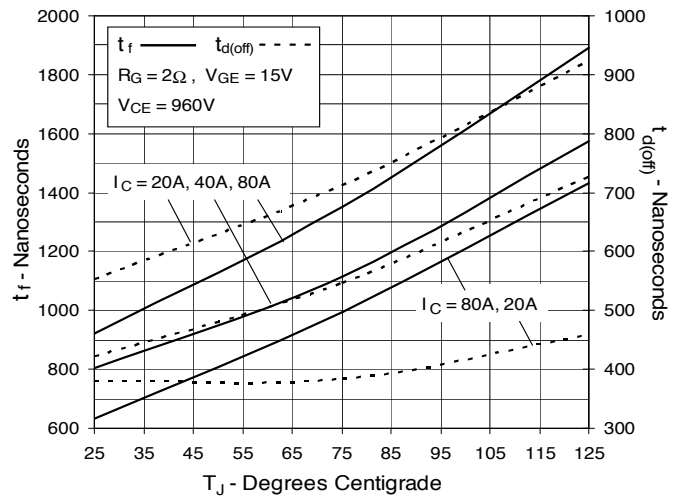


Fig. 11. Inductive Turn-on Switching Times vs. Gate Resistance

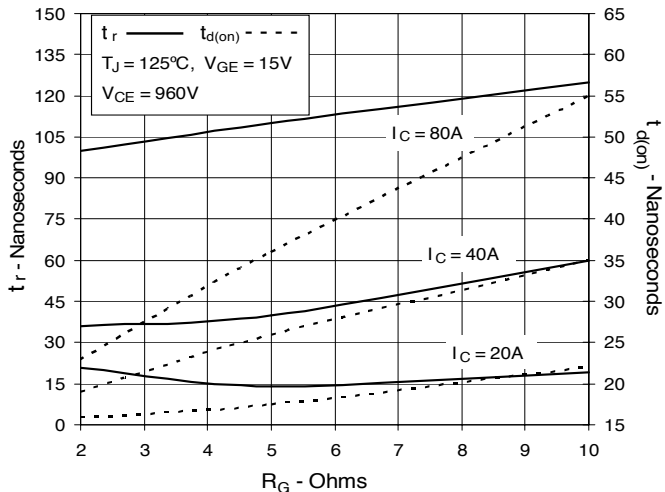


Fig. 12. Inductive Turn-on Switching Times vs. Collector Current

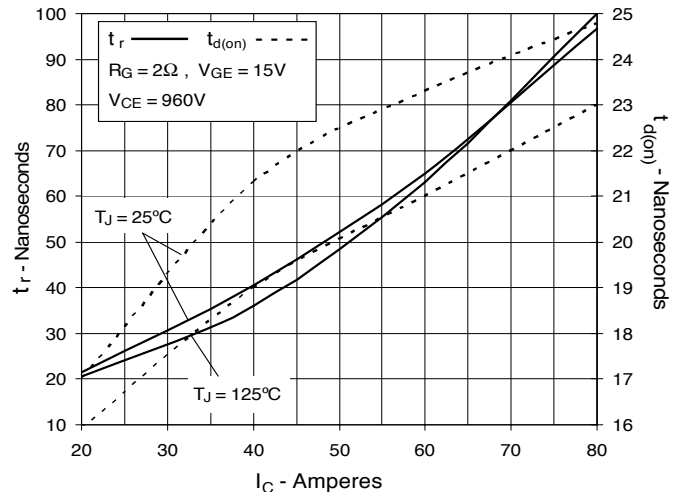


Fig. 13. Inductive Turn-on Switching Times vs. Junction Temperature

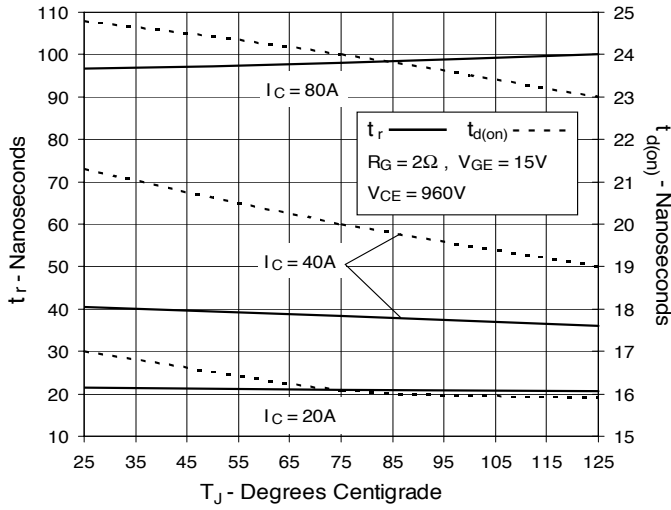


Fig. 14. Gate Charge

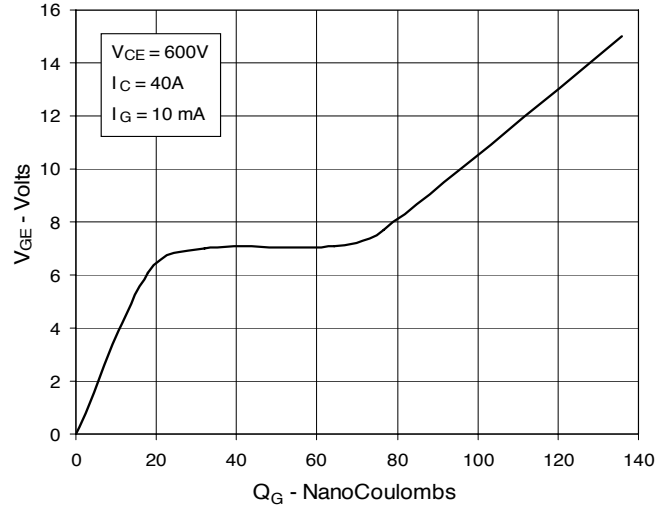


Fig. 15. Capacitance

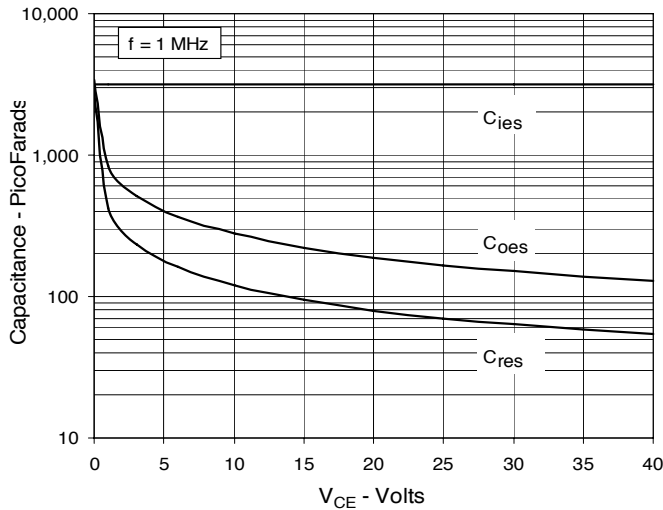


Fig. 16. Reverse-Bias Safe Operating Area

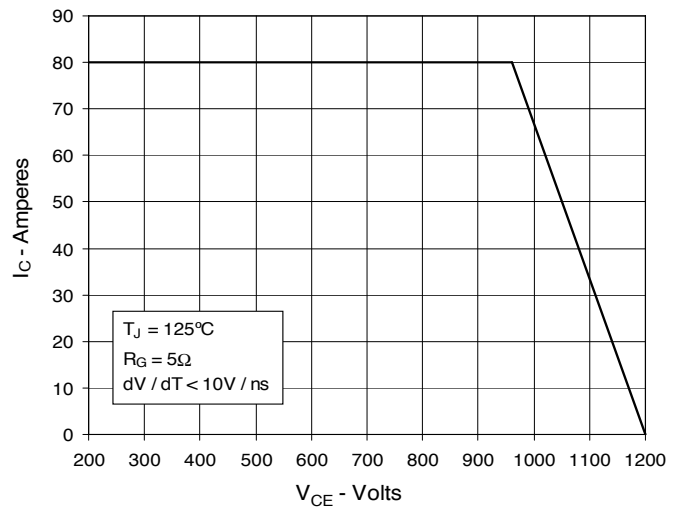
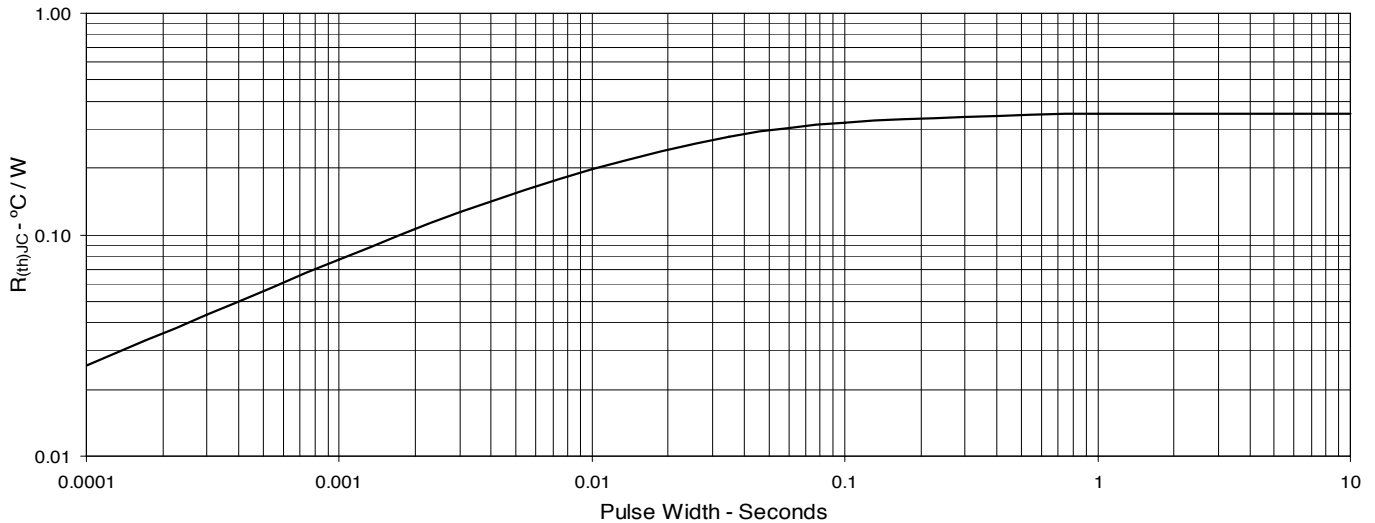


Fig. 17. Maximum Transient Thermal Resistance



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